

Cleaning Rules for Fluorine ICP Etch tool.

Effective immediately. After all etches in the Fluorine ICP etch tool you must run the cleaning recipe:

O2-Clean-USEME-STD

(Copy this recipe into your personal recipe folder and adjust time there)

Do not use any other clean programs following your etching.

Clean times will be set by the following rules:

CHF3/O2 or CHF3/CF4/O2 recipes: 1 minute clean for 1 minute etch, 5 minutes minimum

C4F8/SF6/Ar Si etch recipes: 1 minute clean for 1 minute etch, 5 minutes minimum

C4F8/Ar or C4F8 or C4F8/O2: 5 minutes (yes 5 minutes) clean for 1 minute of etch, no exceptions!

Limit etch time to 10 minutes maximum before cleaning for C4F8/Ar based recipes.

These clean recipes are verified by plasma optical monitoring during the clean cycle testing.

Please plan signup times to account for time needed to clean. User are responsible for